

General Description

The WST4045 is the highest performance trench P-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WST4045 meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

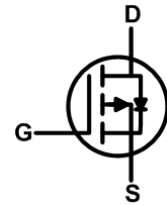
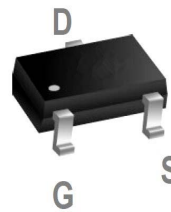
Product Summary

BVDSS	RDSON	ID
-40V	73mΩ	-4.3A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter.
- Networking DC-DC Power System
- Load Switch

SOT-23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-4.3	A
I_{DP}	Pulsed Drain Current	-20	A
P_D	Total Power Dissipation	2.0	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	125	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-40	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.03	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-3A	---	73	85	mΩ
		V _{GS} =-4.5V, I _D =-1A	---	98	126	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	-1.5	-3.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	4.56	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-28V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =-28V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	---	10	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	3.8	---	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-20V, V _{GS} =-10V, I _D =-3.1A	---	14	---	nC
Q _{gs}	Gate-Source Charge		---	2.9	---	
Q _{gd}	Gate-Drain Charge		---	3.8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-20V, V _{GS} =-10V, R _G =3Ω, R _L =2Ω	---	9	---	ns
T _r	Rise Time		---	8	---	
T _{d(off)}	Turn-Off Delay Time		---	28	---	
T _f	Fall Time		---	10	---	
C _{iss}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1MHz	---	650	---	pF
C _{oss}	Output Capacitance		---	90	---	
C _{rss}	Reverse Transfer Capacitance		---	70	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	-4.3	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-2.5A	---	---	-1.2	V

Note :

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

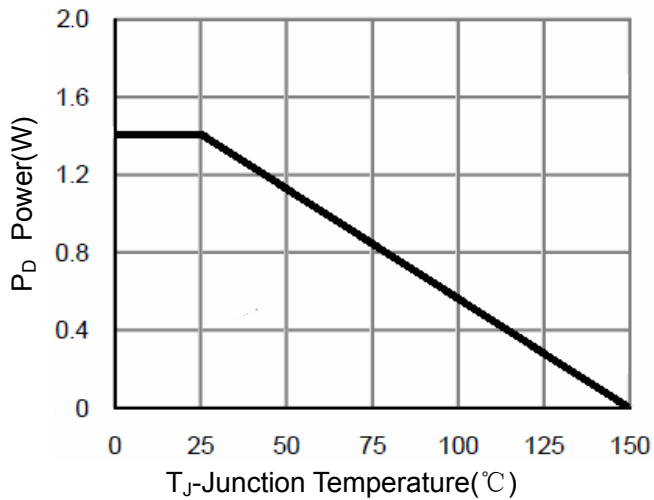


Figure 3 Power Dissipation

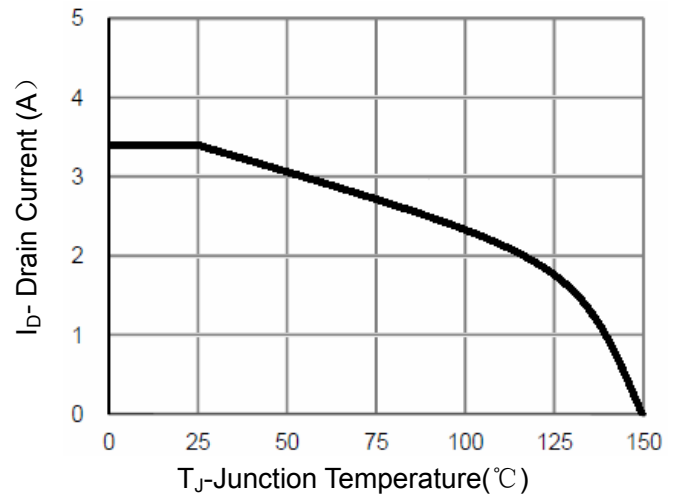


Figure 4 Drain Current

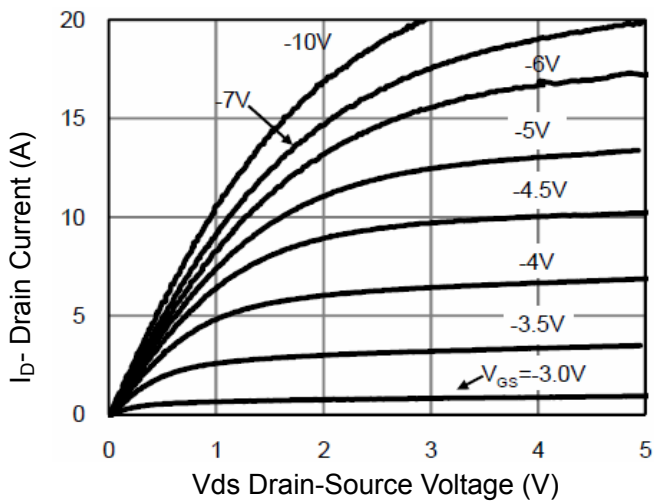


Figure 5 Output Characteristics

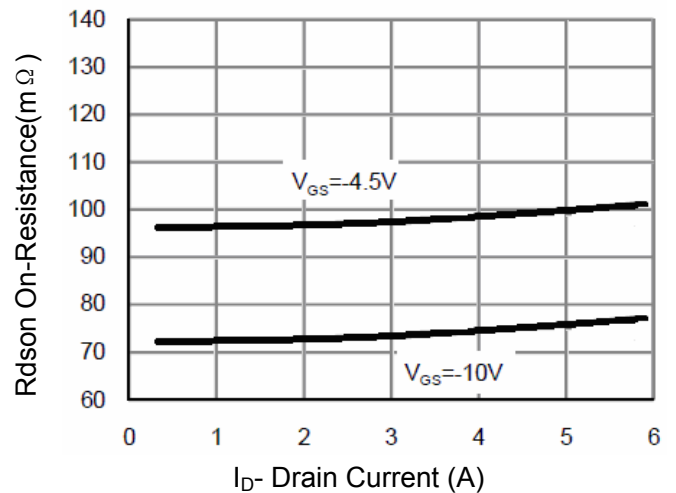


Figure 6 Drain-Source On-Resistance

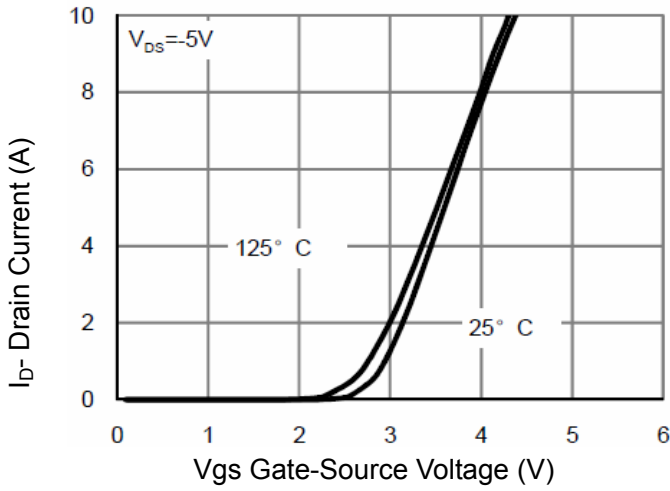


Figure 7 Transfer Characteristics

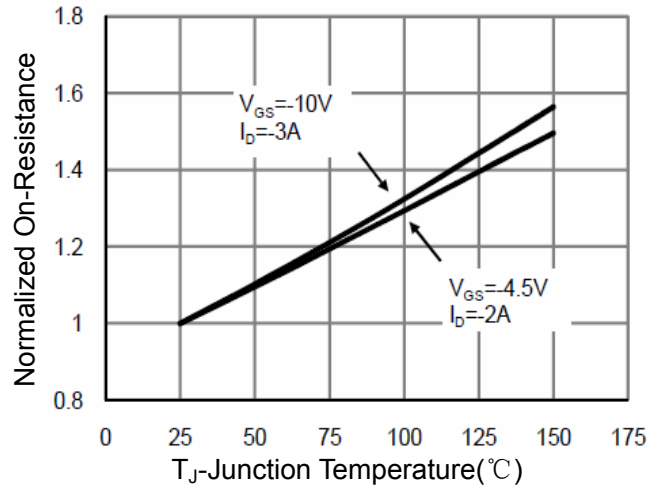


Figure 8 Drain-Source On-Resistance

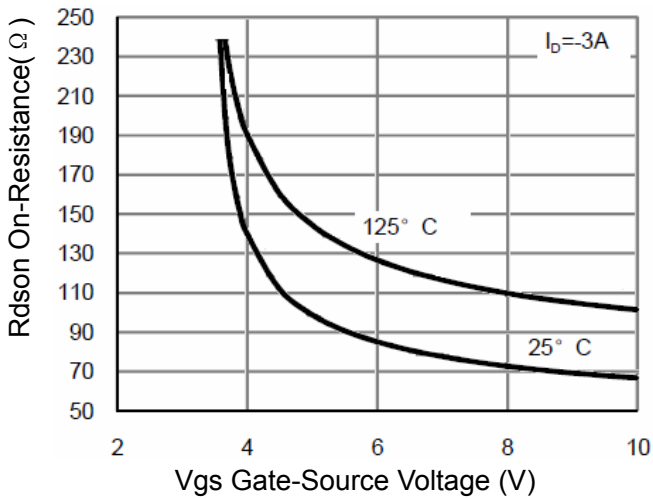


Figure 9 Rdson vs Vgs

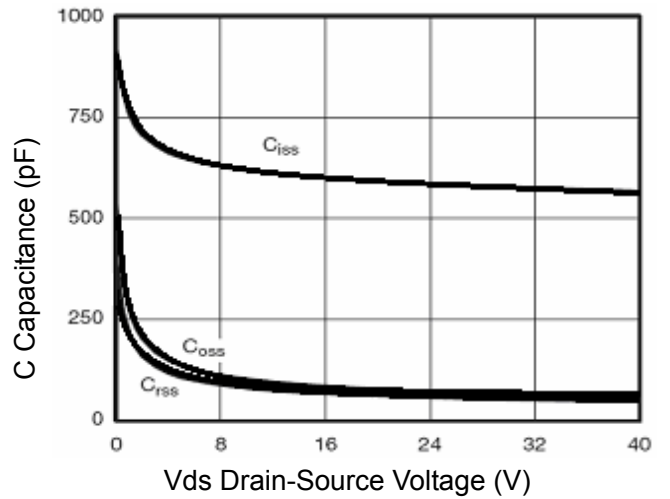


Figure 10 Capacitance vs Vds

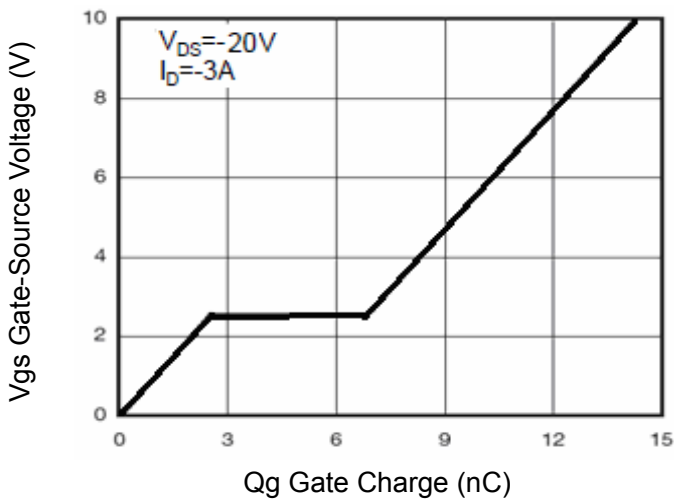


Figure 11 Gate Charge

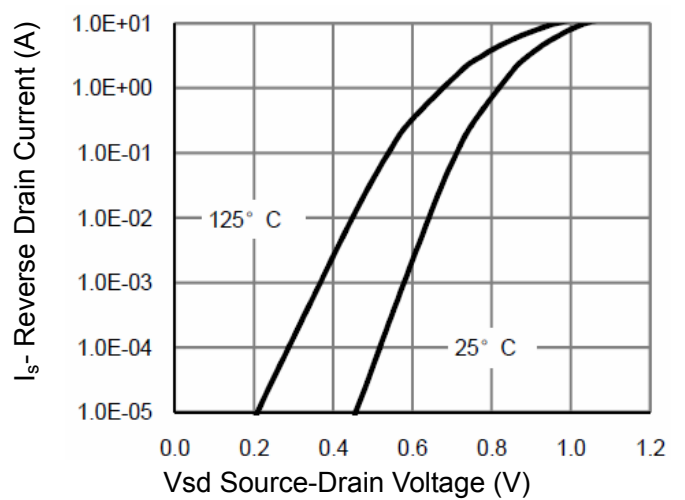


Figure 12 Source- Drain Diode Forward

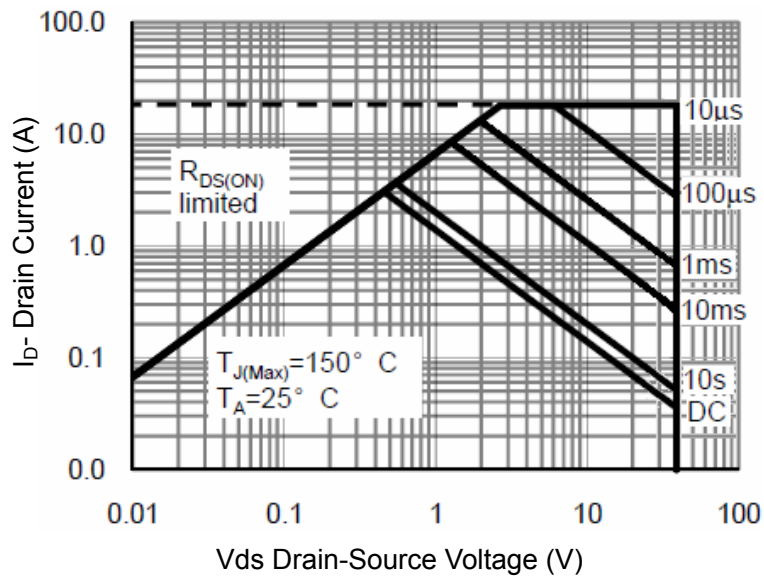


Figure 13 Safe Operation Area

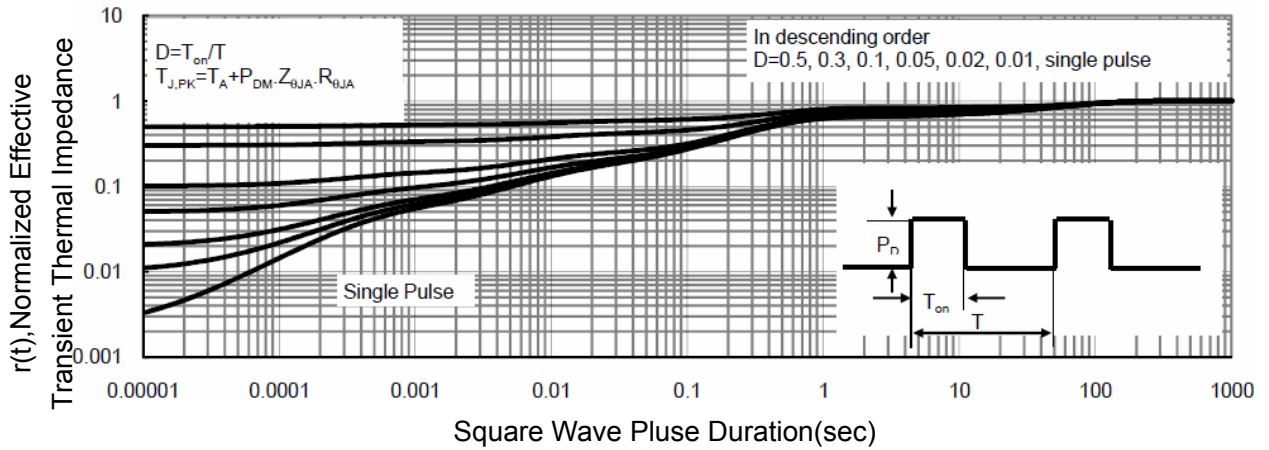


Figure 14 Normalized Maximum Transient Thermal Impedance



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